

DZTA92

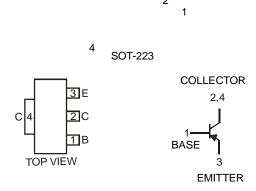
PNP SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DZTA42)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings $@T_A = 25$ °C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	-300	V	
Collector-Emitter Voltage	V _{CEO}	-300	V	
Emitter-Base Voltage	V _{EBO}	-5	V	
Base Current	I _B	-100	mA	
Continuous Collector Current	Ic	-500	mA	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @ T _A = 25℃ (Note 3)	P _d	1	W
Thermal Resistance, Junction to Ambient @ T _A = 25℃ (Note 3)	$R_{ hetaJA}$	125	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-300	_	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-300	_	_	V	$I_C = -1 \text{ mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector-Base Cut-Off Current	I _{CBO}	_	_	-0.25	μΑ	$V_{CB} = -200V, I_{E} = 0$
Emitter-Base Cut-Off Current	I _{EBO}	_	_	-0.1	μΑ	$V_{EB} = -3V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	-0.5	V	$I_C = -20mA$, $I_B = -2mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}		_	-0.9	V	$I_C = -20 \text{mA}, I_B = -2 \text{mA}$
		25	_	_		$I_C = -1 \text{mA}, V_{CE} = -10 \text{V}$
DC Current Gain	h _{FE}	40	_	_	V	$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$
		25	_	_		$I_C = -30 \text{mA}, V_{CE} = -10 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Gain-Bandwidth Product	f _T	50	_	_	MHz	$I_C = -10 \text{mA}, V_{CE} = -20 \text{V}, f = 100 \text{MHz}$
Output Capacitance	C _{obo}			6	pF	$V_{CB} = -20V$, $f = 1MHz$

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB, 1" x 0.85" x 0.052"; pad layout as shown on page 4 or on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Measured under pulsed conditions. Pulse Test: Pulse width, tp<300 uS, Duty Cycle, d< = 2%

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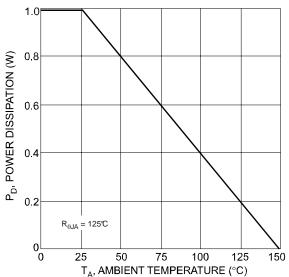


Fig. 1, Power Dissipation vs. Ambient Temperature (Note 3)

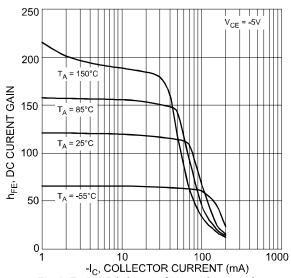
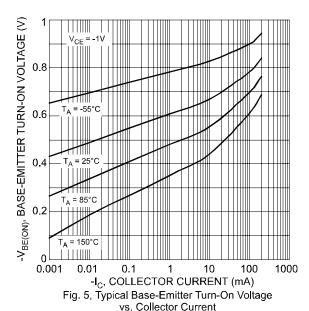


Fig. 3, Typical DC Current Gain vs. Collector Current



0.2 I_B = -10mA = -8m. Ic, COLLECTOR CURRENT (A) 0.15 I_B = -6mA 0.1 $I_B = -2mA$ $I_B = -1mA$ 0.05 0 1 2 3 4 5 -V_{CE}, COLLECTOR-EMITTER VOLTAGE (V) Fig. 2, Typical Collector Current vs. Collector-Emitter Voltage

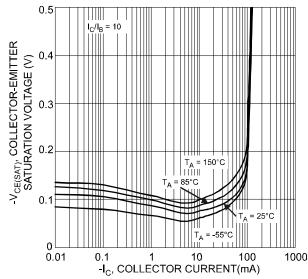


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

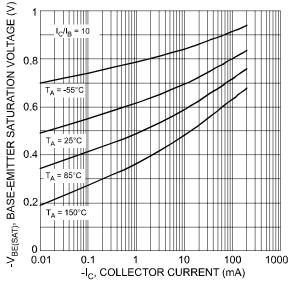
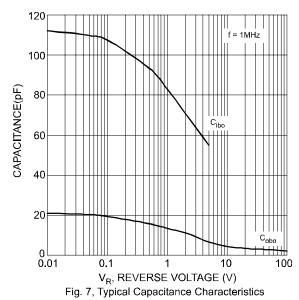


Fig. 6, Typical Base-Emitter Saturation Voltage vs. Collector Current





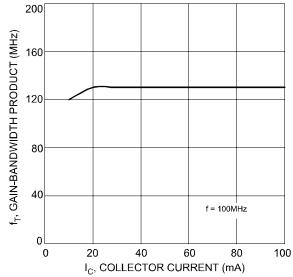


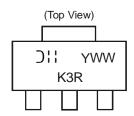
Fig. 8, Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DZTA92-13	SOT-223	2500/Tape & Reel

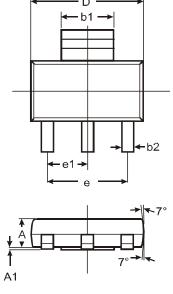
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

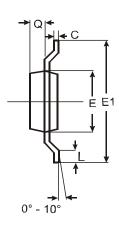
Marking Information



K3R = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

Package Outline Dimensions

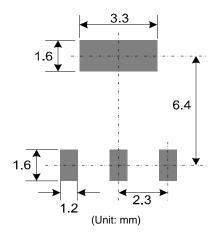




SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е		_	4.60		
e1		_	2.30		
L	0.55	0.75	0.65		
Q	0.84	0.94	0.89		
All Dimensions in mm					



Suggested Pad Layout: (Based on IPC-SM-782)



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